



RB751V-40 SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

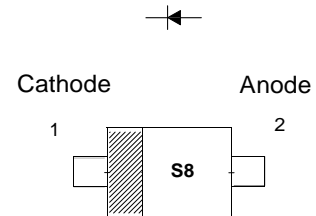
Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching

Marking Code: "S8"



SOD-323

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	0.03	A
Non-repetitive Peak Forward Surge Current@t=8.3ms	I_{FSM}	0.2	A
Power dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	°C/W
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+150	°C

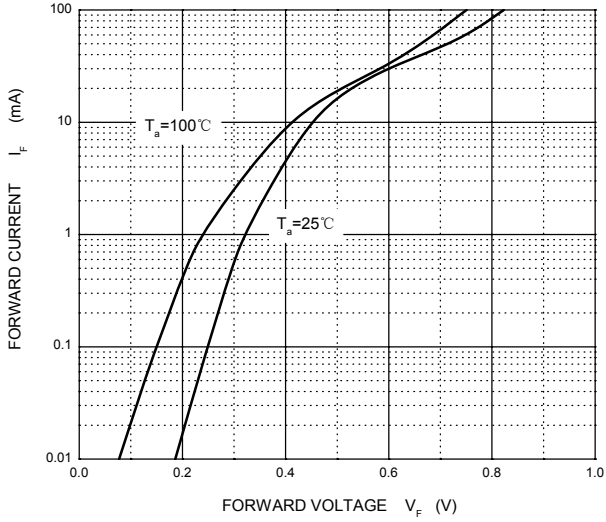
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	0.37	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	0.5	μA
Capacitance Between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	2	-	pF

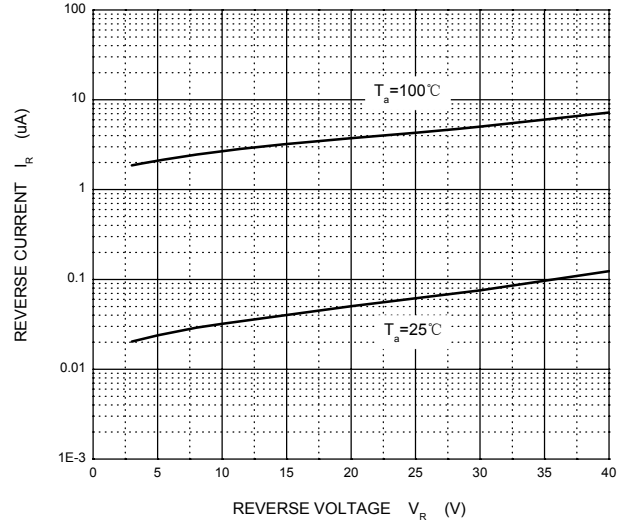
Note: ESD sensitive product handling required.



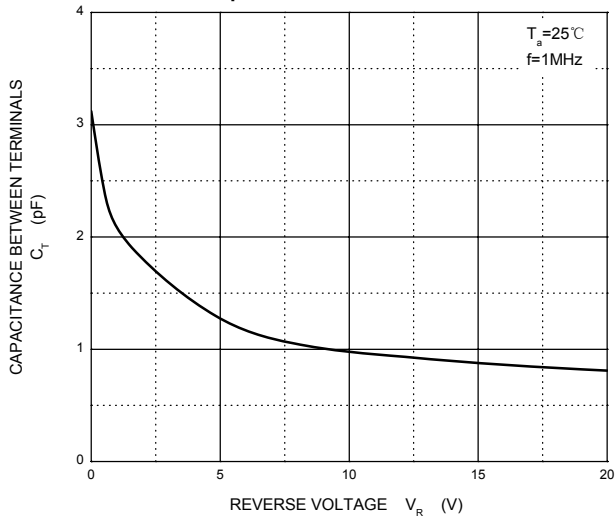
Forward Characteristics



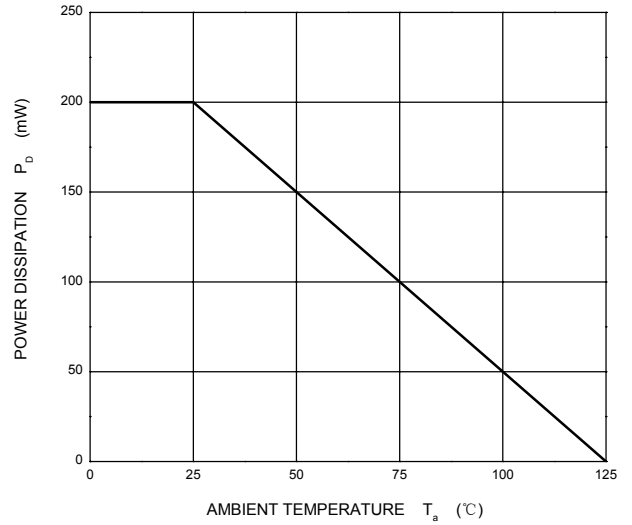
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve





PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

